

BAW56-V

Vishay Semiconductors

Small Signal Switching Diode, Dual

Features

- Silicon Epitaxial Planar Diode
- Fast switching dual diode with common anode
- This diode is also available in other configurations including: a single with type designation BAL99, a dual anode to cathode with type designation BAV99, and a dual common cathode with type designation BAV70.
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

Mechanical Data

Case: SOT23 Plastic case

Weight: approx. 8.8 mg

Packaging Codes/Options:

GS18 / 10 k per 13" reel (8 mm tape), 10 k/box GS08 / 3 k per 7" reel (8 mm tape), 15 k/box

Parts Table

Part	Ordering code	Marking	Remarks
BAW56-V	BAW56-V-GS18 or BAW56-V-GS08	JD	Tape and Reel

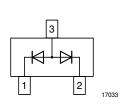
Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Repetitive peak reverse voltage = Working peak reverse voltage = DC Blocking voltage		$V_{R} = V_{RRM}$	70	V
Forward continuous current		۱ _F	250	mA
Non repetitive peak forward current	$t_p = 1 \ \mu s$	I _{FSM}	2.0	A
	t _p = 1 ms	I _{FSM}	1.0	A
	t _p = 1 s	I _{FSM}	0.5	A
Power dissipation		P _{tot}	350 ¹⁾	mW

¹⁾ Device on fiberglass substrate, see layout





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Thermal Characteristics

 $T_{amb} = 25 \ ^{\circ}C$, unless otherwise specified

Parameter	Test condition	Symbol Value		Unit
Thermal resistance junction to ambiant air		R _{thJA}	430	K/W
Junction temperature		Tj	150	°C
Storage temperature range		T _{stg}	- 65 to + 150	٥C

¹⁾ Device on fiberglass substrate, see layout

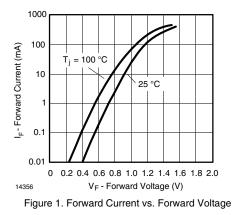
Electrical Characteristics

 $T_{amb} = 25 \ ^{\circ}C$, unless otherwise specified

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
, , , , , , , , , , , , , , , , , , ,	I _F = 1 mA	V _F			715	mV
	I _F = 10 mA	V _F			855	mV
	I _F = 50 mA	V _F			1000	mV
	I _F = 150 mA	V _F			1250	mV
Reverse current	V _R = 70 V	I _R			2.5	μA
	V _R = 70 V, T _j = 150 °C	I _R			100	μΑ
	V _R = 25 V, T _j = 150 °C	I _R			30	μΑ
Diode capacitance	$V_F = V_R = 0$, f = 1 MHz	C _{tot}			2	pF
Reverse recovery time	$I_F = 10 \text{ mA to } I_R = 1 \text{ mA},$ $V_R = 6 \text{ V}, \text{ R}_L = 100 \Omega$	t _{rr}			6	ns

Typical Characteristics

 T_{amb} = 25 °C, unless otherwise specified



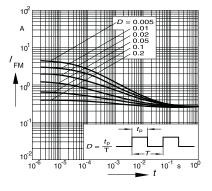
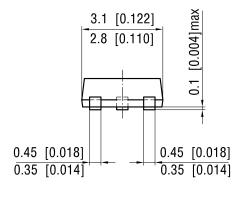


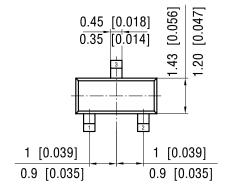
Figure 2. Peak forward current $I_{FM} = f(t_p)$

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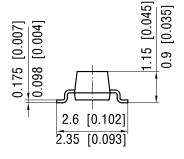


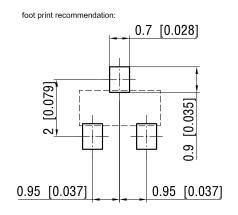
Package Dimensions in mm (Inches)





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Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

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